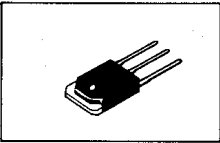


No.1398



# 2SC3483

NPN Triple Diffused Planar Type Silicon Transistor  
 FOR HIGH DEFINITION CRT DISPLAY HORIZONTAL  
 DEFLECTION OUTPUT APPLICATIONS

**Features:**

- High breakdown voltage and high reliability
- High switching speed:  $t_f=0.3\mu s$  max.
- Capable of being mounted easily due to one-point fixing type plastic mold package

**Absolute Maximum Ratings at  $T_a=25^\circ C$**

			unit
Collector to Base Voltage	V <sub>CB0</sub>	1500	V
Collector to Emitter Voltage	V <sub>CE0</sub>	800	V
Emitter to Base Voltage	V <sub>EB0</sub>	7	V
Collector Current	I <sub>C</sub>	2.5	A
Peak Collector Current	i <sub>cp</sub>	10	A
Collector Dissipation	P <sub>C</sub> T <sub>c</sub> =25°C	80	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

**Electrical Characteristics at  $T_a=25^\circ C$**

		min	typ	max	unit
Collector Cutoff Current	I <sub>CB0</sub> V <sub>CB</sub> =800V, I <sub>E</sub> =0			10	uA
Emitter Cutoff Current	I <sub>EB0</sub> V <sub>EB</sub> =5V, I <sub>C</sub> =0			1	mA
DC Current Gain	h <sub>FE</sub> V <sub>CE</sub> =5V, I <sub>C</sub> =0.5A	8			
Gain Bandwidth Product	f <sub>T</sub> V <sub>CE</sub> =10V, I <sub>C</sub> =0.5A		3		MHz
C-E Saturation Voltage	V <sub>CE(sat)</sub> I <sub>C</sub> =2A, I <sub>B</sub> =0.6A			8	V
B-E Saturation Voltage	V <sub>BE(sat)</sub> I <sub>C</sub> =2A, I <sub>B</sub> =0.6A			1.5	V
C-B Breakdown Voltage	V(BR)CBO I <sub>C</sub> =5mA, I <sub>E</sub> =0	1500			V
C-E Breakdown Voltage	V(BR)CEO I <sub>C</sub> =5mA, R <sub>BE</sub> =∞	800			V
E-B Breakdown Voltage	V(BR)EBO I <sub>E</sub> =5mA, I <sub>C</sub> =0	7			V
Storage Time	t <sub>stg</sub> [ I <sub>C</sub> =2A, I <sub>B1</sub> =0.6A ]			3.0	us
Fall Time	t <sub>f</sub> [ I <sub>B2</sub> =-1.2A, R <sub>L</sub> =100ohm ]			0.3	us

**Switching Time Test Circuit**

**Case Outline 2022**  
(unit:mm)

PW=20us, Duty ≤ 1%

